

## INCHANGE SEMICONDUCTOR

# **isc** Silicon NPN Power Transistor

# BD139

#### DESCRIPTION

- DC Current Gain-
  - : hFE= 40(Min)@ IC= 0.15A
- Collector-Emitter Sustaining Voltage : V<sub>CEO(SUS)</sub>= 80V(Min)
- Complement to type BD140
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

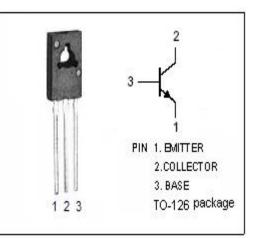
• Designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

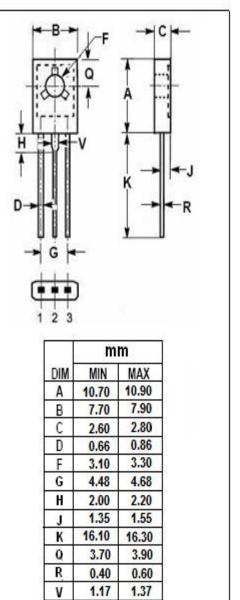
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	100	v				
V <sub>CEO</sub>	Collector-Emitter Voltage	80	v				
V <sub>EBO</sub>	Emitter-Base Voltage	5	V				
Ic	Collector Current-Continuous	1.5	А				
I <sub>B</sub>	Base Current-Continuous	0.5	А				
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.25	w				
	Collector Power Dissipation @ $T_c=25^{\circ}C$	12.5					
TJ	Junction Temperature		°C				
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C				

## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	10	°C/W
R <sub>th j-a</sub>	Rth j-a Thermal Resistance, Junction to Ambient		°C/W





isc website: <u>www.iscsemi.com</u>

<sup>1</sup> *isc & iscsemi* is registered trademark



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## ELECTRICAL CHARACTERISTICS

#### $T_{\text{C}}\text{=}25\,^\circ\!\!\!\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	ΜΙΝ	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA ; I <sub>B</sub> = 0	80			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA			0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 2V			1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30V; I <sub>E</sub> = 0 V <sub>CB</sub> = 30V; I <sub>E</sub> = 0,T <sub>C</sub> =125℃			0.1 10	μA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 5mA ; V <sub>CE</sub> = 2V	25			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 2V	25			
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 0.15A ; V <sub>CE</sub> = 2V	40		250	

#### **NOTICE:**

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